

Jung-Hui Tsai

List of Publications by Year in descending order

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40
papers

111
citations

1651377

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all docs

40
docs citations

40
times ranked

70
citing authors

#	ARTICLE	IF	CITATIONS
1	High-performance InGaP/GaAs pnp $\hat{\Gamma}$ -doped heterojunction bipolar transistor. Semiconductors, 2009, 43, 939-942.	0.2	12
2	Integrated Hydrogen-Sensing Amplifier With GaAs Schottky-Type Diode and InGaP/GaAs Heterojunction Bipolar Transistor. IEEE Electron Device Letters, 2009, 30, 898-900.	2.2	11
3	Performance Improvement of GaN-Based Light-Emitting Diodes With a Microhole Array, 45° Sidewalls, and a SiO ₂ Nanoparticle/Microsphere Passivation Layer. IEEE Transactions on Electron Devices, 2019, 66, 505-511.	1.6	11
4	Performance Enhancement on an InGaP/InGaAs PHEMT With an Electrophoretic Deposition Gate Structure. IEEE Electron Device Letters, 2014, 35, 18-20.	2.2	10
5	Study of a GaN-Based LED With an Al/AZO Composite Transparent Conductive Layer. IEEE Transactions on Electron Devices, 2017, 64, 3678-3682.	1.6	9
6	Characteristics of GaN-Based LEDs With Hybrid Microhole Arrays and SiO ₂ Microspheres/Nanoparticles Structures. IEEE Transactions on Electron Devices, 2017, 64, 2854-2858.	1.6	8
7	Study of a Highly Sensitive Formaldehyde Sensor Prepared With a Tungsten Trioxide Thin Film and Gold Nanoparticles. IEEE Transactions on Electron Devices, 2021, 68, 6422-6429.	1.6	5
8	Comparative investigation of GaAsSb/InGaAs type-II and InP/InGaAs type-I doped-channel field-effect transistors. Semiconductors, 2015, 49, 254-258.	0.2	4
9	Study of a Formaldehyde Gas Sensor Based on a Sputtered Vanadium Pentoxide Thin Film Decorated with Gold Nanoparticles. ECS Journal of Solid State Science and Technology, 2021, 10, 087001.	0.9	4
10	InGaP/InGaAs doped-channel direct-coupled field-effect transistors logic with low supply voltage. Semiconductors, 2010, 44, 223-227.	0.2	3
11	A new InGaP/GaAs tunneling heterostructure-emitter bipolar transistor (T-HEBT). Semiconductors, 2011, 45, 646-649.	0.2	3
12	Comparative investigation of InP/InGaAs abrupt, setback, and heterostructure-emitter heterojunction bipolar transistors. Semiconductors, 2012, 46, 1539-1544.	0.2	3
13	Comparative study of InGaP/GaAs high electron mobility transistors with upper and lower delta-doped supplied layers. Semiconductors, 2012, 46, 514-518.	0.2	3
14	MOS solar cells with oxides deposited by sol-gel spin-coating techniques. Semiconductors, 2013, 47, 835-837.	0.2	3
15	Comparative study of InP/InGaAs double heterojunction bipolar transistors with InGaAsP spacer at base-collector junction. Semiconductors, 2013, 47, 1391-1396.	0.2	3
16	High-performance AlGaIn/AlN/GaN high electron mobility transistor with broad gate-to-source operation voltages. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 596-599.	0.8	3
17	A New Pt-Oxide-InAlP-Based Schottky Diode Hydrogen Sensor. , 2007, , ,		2
18	Comparative investigation of InGaP/GaAs/GaAsBi and InGaP/GaAs heterojunction bipolar transistors. Semiconductors, 2015, 49, 1361-1364.	0.2	2

#	ARTICLE	IF	CITATIONS
19	Temperature-Dependent Study of AlGaAs/InGaAs Integrated Depletion/Enhancement-Mode High Electron Mobility Transistors with Virtual Channel Layers. ECS Journal of Solid State Science and Technology, 2020, 9, 055019.	0.9	2
20	Inverter Logic of AlGaAs/InGaAs Enhancement/Depletion-Mode Pseudomorphic High Electron Mobility Transistors with Virtual Channel Layers. ECS Journal of Solid State Science and Technology, 2019, 8, Q211-Q216.	0.9	2
21	An Optoelectronic Switch with Multiple Operation States. , 2006, , .		1
22	InP/GaAsSb type-II DHBTs with GaAsSb/InGaAs superlattice-base and GaAsSb bulk-base structures. Semiconductors, 2010, 44, 1096-1100.	0.2	1
23	Comparative investigation of InGaP/GaAs pseudomorphic field-effect transistors with triple doped-channel profiles. Semiconductors, 2011, 45, 1231-1233.	0.2	1
24	Comparative investigation of InP/InGaAs heterostructure-emitter tunneling and superlattice bipolar transistors. Semiconductors, 2014, 48, 809-814.	0.2	1
25	An Improved GaN-Based Light-Emitting Diode with a SiO ₂ Current Blocking Layer Embedded in Stair-Like AZO Transparent Structure. ECS Journal of Solid State Science and Technology, 2017, 6, R149-R153.	0.9	1
26	Comparative Studies of AlGaAs/InGaAs Enhancement/Depletion-Mode High Electron Mobility Transistors with Virtual Channel Layers by Hybrid Gate Recesses Approaches. Semiconductors, 2019, 53, 406-410.	0.2	1
27	Comparative Investigation of AlGaN/AlN/GaN High Electron Mobility Transistors with Pd/GaN and Pd/Al ₂ O ₃ /GaN Gate Structures. Science of Advanced Materials, 2021, 13, 289-293.	0.1	1
28	Study of GaN/InGaN Light-Emitting Diodes with Specific Zirconium Oxide (ZrO ₂) Layers. ECS Journal of Solid State Science and Technology, 2022, 11, 075003.	0.9	1
29	An improved InP/InGaAs pnp HBT with δ -doped sheet between emitter-base junction. , 2006, , .		0
30	Investigation of an InGaP/GaAs/InGaAs Step-Emitter Bipolar Transistor. , 2006, , .		0
31	Improved formal passivations of pseudomorphic high electron mobility transistors. , 2008, , .		0
32	Investigation of InP/InGaAs Double Heterojunction Bipolar Transistor (DHBT) with a step-graded InAlGaAs/InP collector structure. , 2008, , .		0
33	An optoelectronic switch. , 2009, , .		0
34	InGaP/GaAs/InGaAs doped-channel field-effect transistor using camel-like gate structure. , 2010, , .		0
35	InGaP/GaAs superlattice-emitter bipolar transistor with InGaAs/GaAs superlattice-base structure. , 2010, , .		0
36	Investigation of InGaP/InGaAs pseudomorphic triple doped-channel field-effect transistors. , 2011, , .		0

#	ARTICLE	IF	CITATIONS
37	MOS solar cells with oxides deposited by sol-gel processing. , 2011, , .		0
38	Influence of gate-to-source and gate-to-drain recesses on GaAs camel-like gate field-effect transistors. Semiconductors, 2014, 48, 1222-1225.	0.2	0
39	Comparative Study of AlGaIn/AlN/GaN Metal-Oxide-Semiconductor High Electron Mobility Transistors with Ni/Au Gate Electrode. ECS Journal of Solid State Science and Technology, 0, , .	0.9	0
40	Pd Nanoparticle/Pd/Al ₂ O ₃ Resistive Sensor for Hydrogen Detection in a High-Temperature Environment. ECS Journal of Solid State Science and Technology, 0, , .	0.9	0